

ABSTRACT OF THE DISCLOSURE

A magnetic memory device includes a memory cell portion, a peripheral circuit portion positioned in the vicinity of the memory cell portion, a plurality of  
5 first magnetoresistive effect elements which are arranged in the memory cell portion and function as memory elements, and a plurality of second magnetoresistive effect elements which are arranged in at least a part of the peripheral circuit portion and  
10 function as dummies, wherein a sum total of occupying areas of the second magnetoresistive effect elements is 5% to 80% of the peripheral circuit portion.